Amendments to the Claims are as follows:

1. (Original) A surface acoustic wave device comprising:

a piezoelectric substrate; and

an electrode section, disposed on the piezoelectric substrate, having a thin-film structure,

wherein the electrode section includes interdigital electrodes and junction electrodes connected to the interdigital electrodes, and the interdigital electrodes each include corresponding first base layers containing Ta and Cu layers or Cu-M alloy layers each disposed on the corresponding first base layers, where M represents one or more elements selected from the group consisting of Ag, Sn, and C.

2. (Currently Amended) The surface acoustic wave device according to Claim 1, wherein the Cu layers or Cu-M alloy layers have a crystal structure in which crystals are oriented in a ~~the~~ (111) direction.

3. (Original) The surface acoustic wave device according to Claim 2, wherein the Cu layers or Cu-M alloy layers have an average grain size ranging from 10 to 100 nm.

4. (Original) The surface acoustic wave device according to Claim 1, wherein the Cu layers or Cu-M alloy layers contain crystal grains having a face-centered cubic structure and the element M is precipitated at grain boundaries.

5. (Currently Amended) The surface acoustic wave device according to Claim 1, wherein the element M is Ag and an~~the~~ Ag content of the Cu-M alloy layers ranges from 0.5 to 10% by mass.

6. (Currently Amended) The surface acoustic wave device according to Claim 5, wherein ~~the element M is Ag and~~ the Ag content of the Cu-M alloy layers ranges from 0.8 to 10% by mass.

7. (Currently Amended) The surface acoustic wave device according to Claim 1, further comprising second base layers each disposed under the corresponding first base layers, wherein the second base layers contain at least one of titanium and/~~or~~ titanium oxides.

8. (Currently Amended) The surface acoustic wave device according to Claim 7, wherein the second base layers have a configuration in which the titanium oxides are disposed on a region containing only titanium and an~~the~~ oxygen content of the titanium oxides gradually increases from ~~the~~ lower faces of the second base layers toward ~~the~~ upper faces.

9. (Original) The surface acoustic wave device according to Claim 1, wherein the first base layers have a thickness ranging from 5 to 15 nm.

10. (Original) The surface acoustic wave device according to Claim 7, wherein the second base layers have a thickness ranging from 3 to 15 nm.

11. (Original) The surface acoustic wave device according to Claim 1, wherein the Cu layers or Cu-M alloy layers have a thickness ranging from 30 to 150 nm.

12. (Original) The surface acoustic wave device according to Claim 1, further comprising protective layers, each disposed on the corresponding Cu layers or Cu-M alloy layers, containing Cr.

13. (Original) A process for manufacturing a surface acoustic wave device comprising the steps of:

forming a multi-layer film including a first base precursor layer containing Ta and a Cu precursor layer or a multi-layer film including the first base precursor layer and a Cu-M alloy precursor layer on a piezoelectric substrate, the first base precursor layer and Cu precursor layer or the first base precursor layer and Cu-M alloy precursor layer being continuously formed;

etching the multi-layer film to form interdigital electrodes;

forming junction electrodes each connected to the corresponding interdigital electrodes; and

heat-treating the piezoelectric substrate having the interdigital electrodes and junction electrodes thereon,

wherein M represents one or more elements selected from the group consisting of Ag, Sn, and C.

14. (Original) The process according to Claim 13, wherein any one of the steps includes a sub-step of forming a protective precursor layer containing Cr on the Cu precursor layer or Cu-M alloy precursor layer.

15. (Currently Amended) The process according to Claim 13, wherein the element M is Ag and an~~the~~ Ag content of the Cu-M alloy precursor layer ranges from 0.5 to 10% by mass.

16. (Currently Amended) The process according to Claim 15, wherein ~~the element M is Ag and~~ the Ag content of the Cu-M alloy precursor layer ranges from 0.8 to 10% by mass.

17. (Currently Amended) The process according to Claim 13, wherein

a~~the~~ temperature of the heat-treating step ranges from 250 to 300°C.

18. (Currently Amended) A process for manufacturing a surface acoustic wave device comprising the steps of:

forming a first~~second~~ base precursor layer containing Ti on a piezoelectric substrate and then exposing the first~~second~~ base precursor layer to ~~the~~ atmosphere;

continuously forming a second~~first~~ base precursor layer containing Ta and a Cu precursor layer on the first~~second~~ base precursor layer or continuously forming the second~~first~~ base precursor layer and a Cu-M alloy precursor layer on the first~~second~~ base precursor layer;

etching the first~~second~~ base precursor layer, second~~first~~ base precursor layer, and Cu precursor layer or etching the first~~second~~ base precursor layer, second~~first~~ base precursor layer, and Cu-M alloy precursor layer to form interdigital electrodes;

forming junction electrodes each connected to the corresponding interdigital electrodes; and

heat-treating the piezoelectric substrate having the interdigital electrodes and junction electrodes thereon,

wherein M represents one or more elements selected from the group consisting of Ag, Sn, and C.

19. (Original) The process according to Claim 18, wherein any one of the steps includes a sub-step of forming a protective precursor layer containing Cr on the Cu precursor layer or Cu-M alloy precursor layer.

20. (Currently Amended) The process according to Claim 18, wherein the element M is Ag and an~~the~~ Ag content of the Cu-M alloy precursor layer

ranges from 0.5 to 10% by mass.

21. (Currently Amended) The process according to Claim 20, wherein ~~the element M is Ag and~~ the Ag content of the Cu-M alloy precursor layer ranges from 0.8 to 10% by mass.

22. (Currently Amended) The process according to Claim 18, wherein a ~~the~~ temperature of the heat-treating step ranges from 250 to 300°C.